

1. Global joint venture starts operations as WeEn Semiconductors

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Thank you for your cooperation and understanding,

WeEn Semiconductors



Product data sheet

1. Product profile

1.1 General description

Ultrafast, dual common cathode, epitaxial rectifier diode in a SOT186A (TO-220F)) plastic package.

1.2 Features

- Fast switching
- Soft recovery characteristics
- Low forward voltage drop
- Low thermal resistance
- Isolated package
- High thermal cycling performance

1.3 Applications

- Output rectifiers in high frequency switched-mode power supplies
- Discontinuous Current Mode (DCM)
 Power Factor Correction (PFC)

1.4 Quick reference data

- $V_{RRM} \le 600 \text{ V}$
- V_F ≤ 1.16 V

- $I_{O(AV)} \le 20 \text{ A}$
- $t_{rr} \le 60 \text{ ns}$

2. Pinning information

Table 1. Pinning

	3		
Pin	Description	Simplified outline	Symbol
1	anode 1		
2	cathode	mb	1
3	anode 2		2
mb	mounting base; isolated		sym084
		SOT186A (3-lead TO-22	0F)



3. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BYV34X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'	SOT186A

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; δ = 1.0; $T_h \le 100~^{\circ}C$	-	600	V
I _{O(AV)}	average output current	square waveform; δ = 0.5; $T_h \leq$ 44 °C; both diodes conducting	-	20	Α
I _{FRM}	repetitive peak forward current	t = 25 μ s; square waveform; δ = 0.5; $T_h \le 44$ °C; per diode	-	20	Α
I _{FSM}	non-repetitive peak forward	t = 10 ms; sinusoidal waveform; per diode	-	120	Α
	current	t = 8.3 ms; sinusoidal waveform; per diode	-	132	Α
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; per diode; see Figure 1	-	-	5.0	K/W
		with heatsink compound; both diodes conducting	-	-	4.0	K/W
		without heatsink compound; per diode	-	-	7.0	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

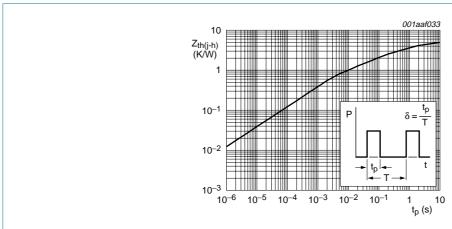


Fig 1. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$ unless otherwise specified.

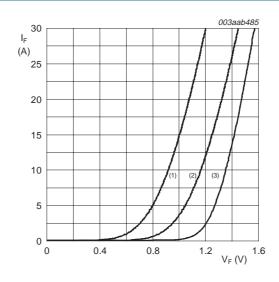
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; $f = 50 \text{ Hz}$ to 60 Hz ; sinusoidal waveform; relative humidity $\leq 65 \%$; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

7. Characteristics

Table 6. Characteristics

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

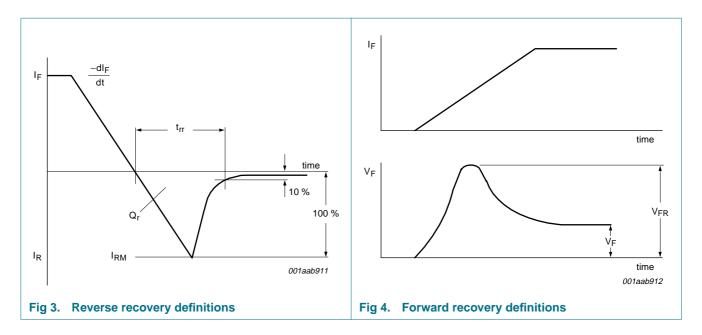
., _0 0	iniess otherwise specified	••				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V_{F}	forward voltage	$I_F = 10 \text{ A}$; $T_j = 150 ^{\circ}\text{C}$; see Figure 2	-	0.92	1.16	V
		I _F = 10 A; see <u>Figure 2</u>	-	1.07	1.36	V
I _R	reverse current	V _R = 600 V	-	10	50	μΑ
		$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.2	0.6	mA
Dynamic o	characteristics					
Q _r	recovered charge	I_F = 2 A to V_R \geq 30 V; dI_F/dt = 20 A/ μ s; see Figure 3	-	40	70	nC
t _{rr}	reverse recovery time	I_F = 1 A to V_R \geq 30 V; dI_F/dt = 100 A/ μ s; see Figure 3	-	50	60	ns
I _{RM}	peak reverse recovery current	I_F = 10 A to V_R \geq 30 V; dI_F/dt = 50 A/ μ s; T_j = 100 °C; see Figure 3	-	3	5	Α
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; see Figure 4	-	3.2	-	V



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values
- (2) $T_j = 150 \,^{\circ}\text{C}$; maximum values
- (3) $T_j = 25$ °C; maximum values

Fig 2. Forward current as a function of forward voltage

Dual rectifier diode ultrafast



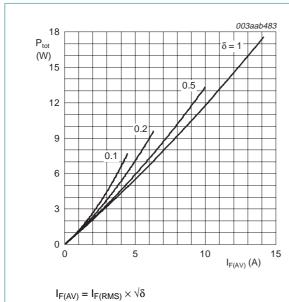
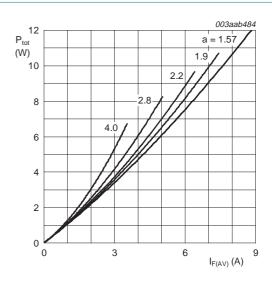


Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values



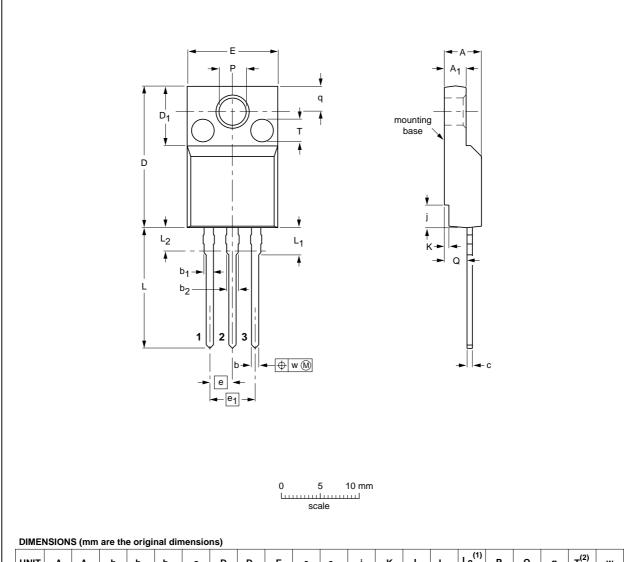
 $a = form factor = I_{F(RMS)} / I_{F(AV)}$

Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



UNIT	Α	A ₁	b	b ₁	b ₂	С	D	D ₁	E	е	e ₁	j	к	L	L ₁	L ₂ ⁽¹⁾ max.	Р	Q	q	T ⁽²⁾	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT186A		3-lead TO-220F			02-04-09 06-02-14

Fig 7. Package outline SOT186A (3-lead TO-220F)



Dual rectifier diode ultrafast

9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV34X-600_1	20070913	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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